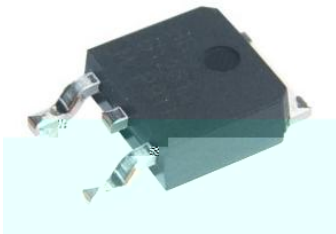
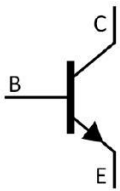


TO-252 NPN Silicon NPN transistor in a TO-252 Plastic Package.

f_T

Low $V_{CE(sat)}$, high current and high f_T , excellent linearity of h_{FE} , fast switching time.

Relay drivers, high-speed inverters, general high-current switching applications.



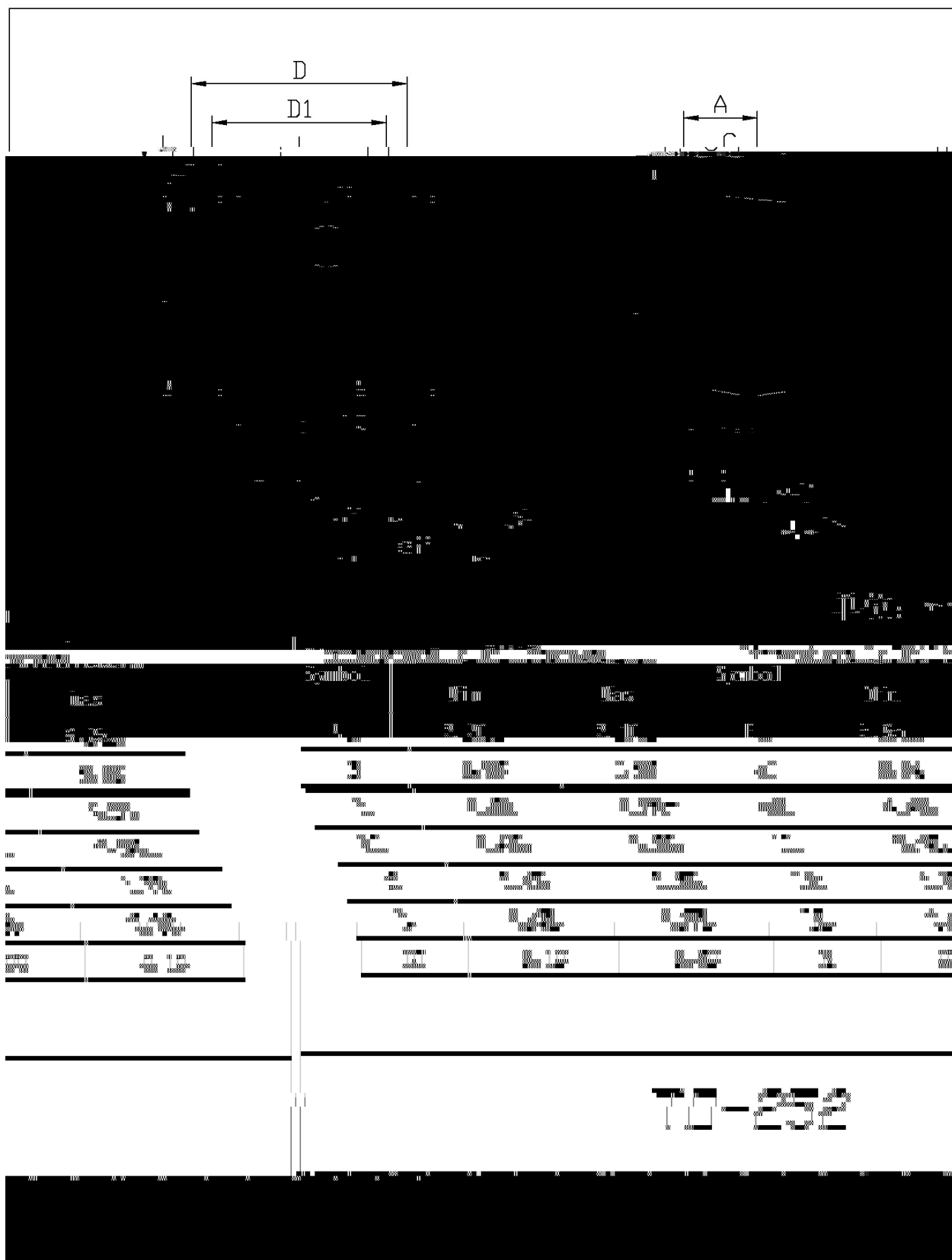
PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current - Continuous	I_C	5	A
Collector Current – Continuous(Pulse)	I_{CP}	8	A
Collector Power Dissipation	P_C	1.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ\text{C})$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

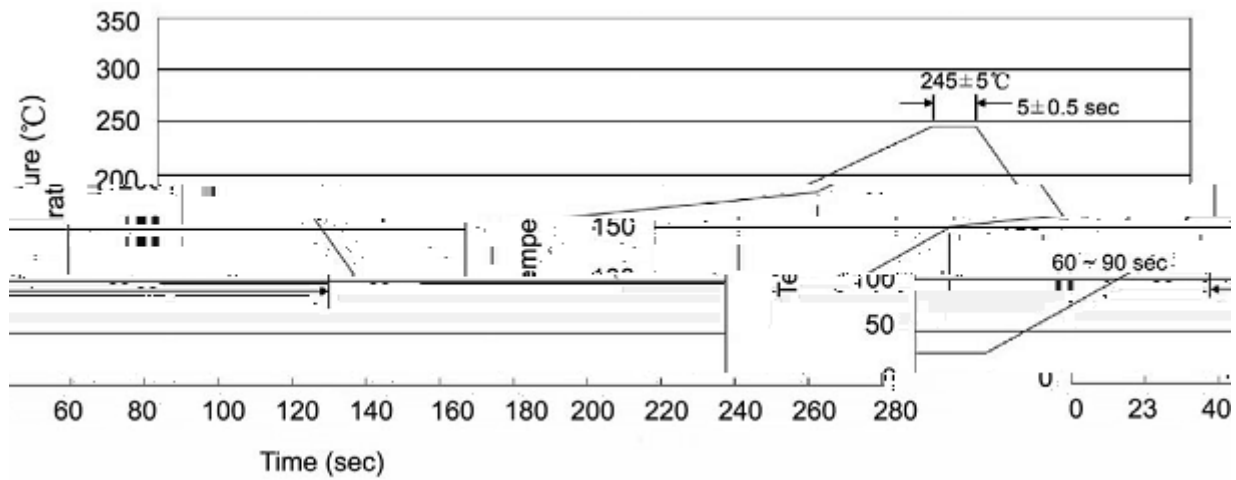
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10\mu\text{A}$ $I_E=0$	60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0\text{mA}$ $R_{BE}=\infty$	50			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\mu\text{A}$ $I_C=0$	6			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=40\text{V}$ $I_E=0$			1.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4.0\text{V}$ $I_C=0$			1.0	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2.0\text{V}$ $I_C=0.5\text{A}$	70		400	V
		$I_C=3.0\text{A}$ $I_B=0.15\text{A}$		0.22	0.4	V_{D0}
	$h_{FE(sat)}$	$I_C=3.0\text{A}$ $I_B=0.15\text{A}$		0.95	1.3	V_{D0}
	T	$V_{CE}=5.0\text{V}$ I_C				

/ Package Dimensions



2SD1803

() /



Note:

- 1

25 150

60 90sec;
- 2

245±5

5±0.5sec;
- 3

2 10 /sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:245±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units				Dimension		(unit mm ³)